

FORM PTO-1449	SERIAL NO. Not yet assigned	CASE NO. 107929049 10808/227
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE Herewith	GROUP ART UNIT Not yet assigned
APPLICANT(S): Ronald Kakoschke		

## REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	A1	US2002/0130354 A1	September 19, 2002	Sekigawa et al.		
	A2	6,369,108 B1	May 28, 2002	Krivokapic et al.		
	A3	5,930,605	July 27, 1999	Mistry et al.		
	A4	5,693,918	November 4, 1997	Smith et al.		
	A5	4,996,574	February 26, 1991	Shirasaki		
	A6	4,965,213	October 23, 1990	Blake		

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.					
	A7	J.M. Hwang, H. Lu, Y.D. Sheu, W. Bailey, P. Mei, G. Pollack, <i>Premature Breakdown in Non-Fully Depleted SOI/Mosfets with Body-Tied-To-Source Structure</i> , pgs. 34-35, SOI Conference, Proceedings. IEEE, October 1, 1991.				
	A8	C.J. Chang-Hasnain, J.P. Harbison, C.E. Zah, L.T. Florez and N.C. Andreadakis, <i>Supression of Latch in SOI Mosfets By Silicidation of Source</i> , pgs. 1003-1005, Electronics Letters, Vol. 27, May 23, 1991.				
	A9	F.L. Duan and D.E. Ioannou, <i>Design and Analysis of a Novel Mixed Accumulations/Inversion Mode FD SOI Mosfet</i> , pgs. 100-101, Proceedings IEEE International SOI Conference, October 1997.				
	A10	S. Cristoloveanu and G. Reichert, <i>Recent Advances in SOI Materials and Device Technologies for High Temperature</i> , pgs. 86-93, High-Temperature Electronics, Materials, Devices and Sensors Conference, IEEE, February 1998.				
	A11	Srinath Krishnan, <i>Efficacy of Body Ties Under Dynamic Switching Conditions in Partially Depleted SOI CMOS Technology</i> , pgs. 140-141, IEEE International SOI Conference, 1997.				
	A12	Jeffrey W. Sleight, <i>DC and Transient Characterization a Compact Schottky Body Contact Technology for SOI Transistors</i> , pgs. 1451-1456, IEEE Transactions on Electron Devices, July, 1999.				
	A13	Copy of International Search Report from corresponding PCT application number PCT/DE03/03131.				
	A14	Copy of Examination Report from corresponding PCT application number PCT/DE03/03131.				

EXAMINER /Sarah Salerno/	DATE CONSIDERED 11/05/2007
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /S.K.S./